1 2 "20010009803"	LIODAT 0004/07/45 40:40
	USPAT; 2004/07/15 18:18
	US-PGPUB;
	EPO; JPO;
	DERWENT;
	IBM_TDB
2 1048   via near12 mu	USPAT; 2004/07/15 18:31
	US-PGPUB;
	EPO; JPO;   DERWENT;
	IBM TDB
3 (via near12 mu) and damascene	USPAT; 2004/07/15 18:40
o (via near 12 ma) and damascene	US-PGPUB;
	EPO; JPO;
	DERWENT;
	IBM_TDB
5 56062 (ang angstrom nm nanometer) near12 (o	
trench via dielectric insulation insulating i	
	ÉPO; JPO;
	DERWENT;
	IBM_TDB
6 34310 (micron mu) near12 (opening hole groove	
insulation insulating insulator ILD)	US-PGPUB;
	EPO; JPO;
	DERWENT;
-	IBM_TDB
7 85504 ((ang angstrom nm nanometer) near12 (	
trench via dielectric insulation insulating i	
((micron mu) near12 (opening hole groov dielectric insulation insulating insulator IL	
dielectric insulation insulating insulator it	IBM TDB
8 8190 (((ang angstrom nm nanometer) near12 (	
trench via dielectric insulation insulating i	
((micron mu) near12 (opening hole groov	
dielectric insulation insulating insulator IL	
inlaid fill\$4) near3 (metal metallization co	,,,
Cu)) or damascene)	_
9 6410 ((((ang angstrom nm nanometer) near12	
groove trench via dielectric insulation insu	
ILD)) ((micron mu) near12 (opening hole	
dielectric insulation insulating insulator IL	
inlaid fill\$4) near3 (metal metallization co	
Cu)) or damascene)) and (257/\$ or 438/\$	
10 3863 (((ang angstrom nm nanometer) near12 ( trench via dielectric insulation insulating i	1 0 0 1 1
((micron mu) near12 (opening hole groov	
dielectric insulation insulating insulator IL	
damascene	IBM_TDB
11 3393 ((((ang angstrom nm nanometer) near12	
groove trench via dielectric insulation insu	ulating insulator US-PGPUB;
ILD)) ((micron mu) near12 (opening hole	
dielectric insulation insulating insulator IL	
damascene) and (257/\$ or 438/\$).ccls.	IBM_TDB
12 2376 (((ang angstrom nm nanometer) near12 (	
trench via dielectric insulation insulating i	
((micron mu) near12 (opening hole groov	
dielectric insulation insulating insulator IL	
damascene) 13 402 ((((ang angstrom nm nanometer) near12	IBM_TDB
13   402   ((((ang angstrom nm nanometer) near12   groove trench via dielectric insulation inst	
ILD)) ((micron mu) near12 (opening hole	
dielectric insulation insulating insulator IL	
i i ulelectric insulation insulating insulation in	

14	257	((((ang angstrom nm nanometer) near12 (opening hole	USPAT:	2004/07/15 18:43
• •	20,	groove trench via dielectric insulation insulating insulator	US-PGPUB;	200
		ILD)) ((micron mu) near12 (opening hole groove trench via	EPO; JPO;	
		dielectric insulation insulating insulator ILD))) and (dual adj	DERWENT;	
		damascene)) and @rlad<19990630	IBM_TDB	
15	595	(((((ang angstrom nm nanometer) near12 (opening hole	USPAT;	2004/07/15 19:26
		groove trench via dielectric insulation insulating insulator	US-PGPUB;	
		ILD)) ((micron mu) near12 (opening hole groove trench via	EPO; JPO;	
		dielectric insulation insulating insulator ILD))) and (dual adj	DERWENT;	
		damascene)) and @ad<19990630) (((((ang angstrom nm	IBM_TDB	
		nanometer) near12 (opening hole groove trench via dielectric		
		insulation insulating insulator ILD)) ((micron mu) near12		
		(opening hole groove trench via dielectric insulation insulating insulator ILD))) and (dual adj damascene)) and		
		@rlad<19990630)		
16	0	".mu."	USPAT:	2004/07/15 19:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
17	16292	\$3mu near12 (opening hole groove trench via dielectric	USPAT;	2004/07/15 19:27
		insulation insulating insulator ILD)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
40	/ 00	(62m), page 12 (anguing hala graphs transhivin dialoctria	IBM_TDB	2004/07/15 19:30
18	26	(\$3mu near12 (opening hole groove trench via dielectric insulation insulating insulator ILD)) and (dual adj damascene)	USPAT; US-PGPUB;	2004/01/15 19.50
		Insulation insulating insulator IED/) and (dual adj damascene)	EPO; JPO;	
	1		DERWENT;	
			IBM TDB	